

1.Description

The UMW SN74LVC2G34 is a high performance dual buffer operating from a 1.65 to 5.5 V supply. This device is fabricated with advanced CMOS technology to achieve ultra-high speed with high output drive.

2.Features

- Designed for 1.65V to 5.5V V_{CC} Operation
- Overvoltage Tolerant Inputs
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- These Devices are Pb-Free and are RoHS Compliant

3.Pinning information

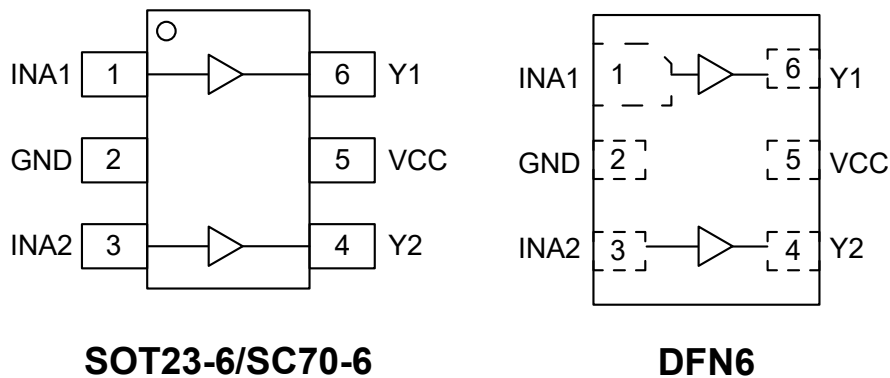


Figure1. Top View



4.Pin Function

Pin	Function
1	INA1
2	GND
3	INA2
4	Y2
5	VCC
6	Y1



5.Block Diagram

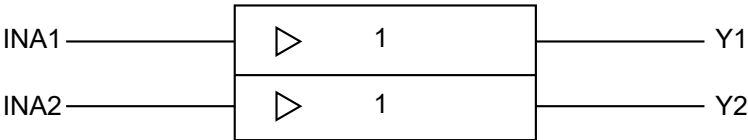


Figure2. Logic Symbol

Function Table

Input	Output
A	Y
L	L
H	H



6. Absolute Maximum Ratings

Parameter		Symbol	Value	Units
DC Supply Voltage		V_{CC}	-0.5 to 7	V
DC Input Voltage		V_I	$-0.5 \leq V_I \leq 7$	V
DC Output Voltage Output in Higher or Low State (Note 1)		V_O	-0.5 to $V_{CC} + 0.5$	V
DC Input Diode Current $V_I < GND$		I_{IK}	-50	mA
DC Output Diode Current $V_O < GND$, $V_O > V_{CC}$		I_{OK}	± 50	mA
DC Output Sink Current		I_O	± 50	mA
DC Supply Current per Supply Pin		I_{CC}	± 100	mA
Storage Temperature Range		T_{STG}	-65 to 150	°C
Lead Temperature, 1 mm from Case for 10 Seconds		T_L	260	°C
Junction Temperature Under Bias		T_J	150	°C
Thermal Resistance	SC70-6	θ_{JA}	333	°C/W
	SOT23-6		225	°C/W
	DFN6		423	°C/W
Power Dissipation in Still Air at 85°C		P_D	200	mW
Moisture Sensitivity		MSL	Level 1	
ESD Classification Human	Body Model (Note 2)	ESD	2000	V
	Machine Model (Note3)		200	V
	Charged Device Model (Note 4)		N/A	V
Latchup Performance Above V_{CC} and Below GND at 125°C (Note 5)		$I_{Latchup}$	± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. IO absolute maximum rating must be observed.
2. Tested to EIA/JESD22—A114—A, rated to EIA/JESD22—A114—B.
3. Tested to EIA/JESD22—A115—A, rated to EIA/JESD22—A115—A.
4. Tested to JESD22—C101—A.
5. Tested to EIA/JESD78.



7. Recommended Operating Conditions

Parameter		Symbol	Min	Max	Unit
DC Supply Voltage Operating		V _{CC}	1.65	5.5	V
Data Retention			1.5	5.5	V
DC Input Voltage		V _{IN}	0	5.5	V
DC Output Voltage (High or Low State)		V _{OUT}	0	5.5	V
Operating Temperature Range		T _A	-40	85	°C
Input Rise and Fall Time	V _{CC} =2.5V ± 0.2V	t _r , t _f	0	20	ns/V
	V _{CC} =3V ± 0.3V		0	10	ns/V
	V _{CC} =5V ± 0.5V		0	5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied.



8.DC Electrical Characteristics

Parameter	Condition	Symbol	$V_{CC}(V)$	$T_A=25^{\circ}C$			$-55^{\circ}C \leq T_A \leq 85^{\circ}C$		Units
				Min	Typ	Max	Min	Max	
High-Level Input Voltage		V_{IH}	1.65 to 1.95	$0.75V_{CC}$			$0.75V_{CC}$		V
			2.3 to 5.5	$0.7V_{CC}$			$0.7V_{CC}$		
Low-Level Input Voltage		V_{IL}	1.65 to 1.95			$0.25V_{CC}$		$0.25V_{CC}$	
			2.3 to 5.5			$0.3V_{CC}$		$0.3V_{CC}$	
High-Level Output Voltage $V_{IN}=V_{IL}$	$I_{OH}=-100\mu A$	V_{OH}	1.65 to 5.5	$V_{CC}-0.1$	V_{CC}		$V_{CC}-0.1$		V
	$I_{OH}=-3mA$		1.65	1.29	1.52		1.29		
	$I_{OH}=-8mA$		2.3	1.9	2.1		1.9		
	$I_{OH}=-12mA$		2.7	2.2	2.4		2.2		
	$I_{OH}=-16mA$		3	2.4	2.7		2.4		
	$I_{OH}=-24mA$		3	2.3	2.5		2.3		
	$I_{OH}=-32mA$		4.5	3.8	4		3.8		
Low-Level Output Voltage $V_{IN}=V_{IH}$	$I_{OH}=100\mu A$	V_{OL}	1.65 to 5.5		0.0	0.1		0.1	V
	$I_{OL}=3mA$		1.65		0.08	0.24		0.24	
	$I_{OL}=8mA$		2.3		0.2	0.3		0.3	
	$I_{OL}=12mA$		2.7		0.22	0.4		0.4	
	$I_{OL}=16mA$		3		0.28	0.4		0.4	
	$I_{OL}=24mA$		3		0.38	0.55		0.55	
	$I_{OL}=32mA$		4.5		0.42	0.55		0.55	
Input Leakage Current	$V_{IN}=5.5V$ or GND	I_{IN}	0 to 5.5		± 0.1			± 1	μA
Power Off Leakage Current	$V_{IN}=5.5V$ or $V_{OUT}=5.5V$	I_{OFF}	0			1		10	
Quiescent Supply Current	$V_{IN}=5.5V$ or GND	I_{CC}	5.5			1		10	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



9.AC Electrical Characteristics

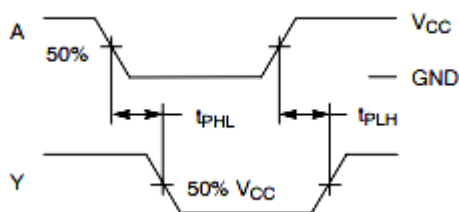
Parameter	Condition	Symbol	V _{CC} (V)	T _A =25°C			-40°C≤T _A ≤85°C		Units
				Min	Typ	Max	Min	Max	
Propagation Delay (Figure 3 and 4)	R _L =1MΩ, C _L =15pF	t _{PLH} , t _{PHL}	1.65	2	10.1	12.9	2	13.9	ns
			1.8	2	9.1	11.6	2	12.4	
			2.5	0.2	6	7.7	0.8	8.2	
			3.3	0.8	5	6.5	0.5	7	
	R _L =500Ω, C _L =50pF		3.3	1.2	5.6	7.1	1.5	7.6	
	R _L =1MΩ, C _L =15pF		5.0	0.5	4.4	5.6	0.5	6.1	
	R _L =500Ω, C _L =50pF		5.0	0.8	4.8	6.1	0.8	6.6	

10.Capacitance Characteristics

Parameter	Symbol	Condition	Typ	Units
Input Capacitance	C _{IN}	V _{CC} =5.5V, V _I = 0V or V _{CC}	>2.5	pF
Power Dissipation Capacitance ⁽⁶⁾	C _{PD}	10MHz, V _{CC} =3.3V, V _I =0V or V _{CC}	15	pF
		10MHz, V _{CC} =5.5V, V _I =0V or V _{CC}	17	pF

Notes 6:

C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)}=C_{PD}*V_{CC}*fin+I_{CC}*C_{PD} is used to determine the no-load dynamic power consumption; P_D=C_{PD}*V_{CC}²*fin+I_{CC}*V_{CC}*Fig.



PROPAGATION DELAYS

 $t_R = t_F = 2.5 \text{ ns, 10% to 90%};$
 $f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 3. switching Waveforms

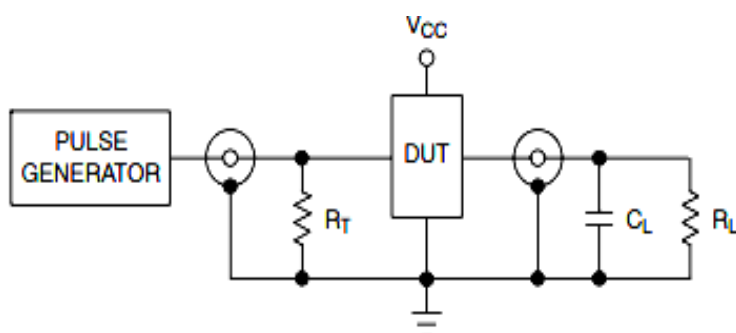
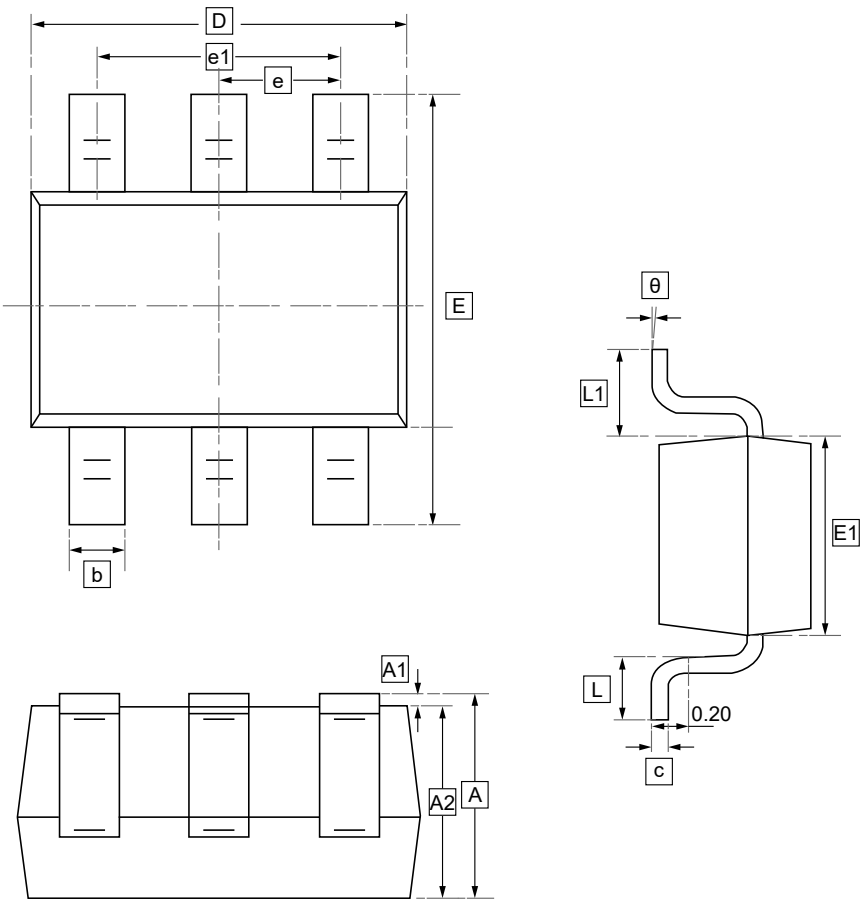

 $R_T = 50 \Omega (\text{typ})$

Figure 4. Test Circuit



11.1 SC70-6 Package Outline Dimensions



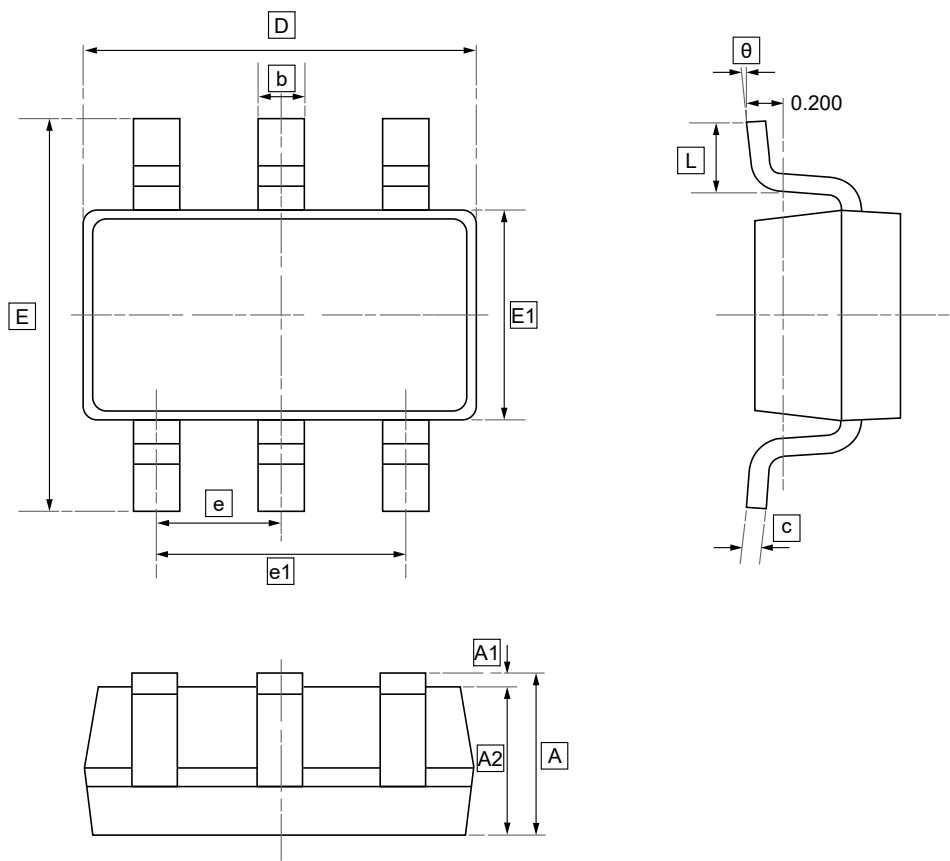
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E	E1	e	e1	L	L1
Min	0.90	0.00	0.90	0.15	0.08	2.05	2.15	1.15	0.65	1.2	0.26	0.525
Max	1.10	0.10	1.00	0.35	0.15	2.25	2.45	1.35	TYP.	1.4	0.46	REF.

Symbol	θ
Min	0°
Max	8°



11.2 SOT23-6 Package Outline Dimensions

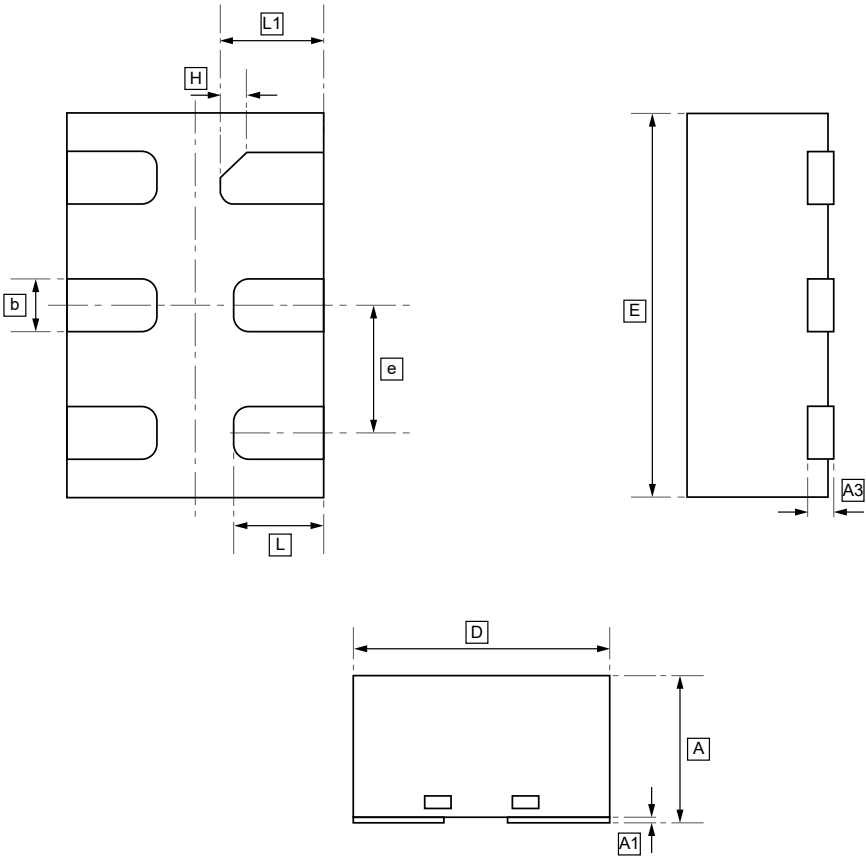


DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E1	E	e	e1	L	θ
Min	1.050	0.000	1.050	0.300	0.100	2.820	1.500	2.650	0.950	1.800	0.300	0°
Max	1.250	0.100	1.150	0.500	0.200	3.020	1.700	2.950	BSC	2.000	0.600	8°



11.3 DFN6(1*1.5) Package Outline Dimensions

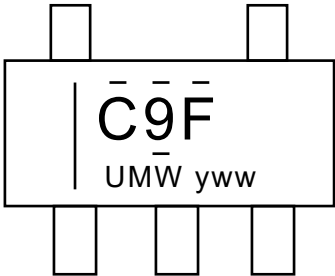


DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A3	b	D	E	e	H	L	L1
Min	0.50	0	0.10	0.15	0.90	1.40	0.40	0.10	0.30	0.35
Max	0.60	0.05	REF	0.25	1.10	1.60	0.60	REF	0.40	0.45



12.Ordering information



yww: Batch Code

Order Code	Marking	Package	Base QTY	Delivery Mode
UMW SN74LVC2G34DBVR	C345	SOT23-6	3000	Tape and reel
UMW SN74LVC2G34DCKR	C9F	SC70-6	3000	Tape and reel
UMW SN74LVC2G34DRYR	C9	DFN6	5000	Tape and reel



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